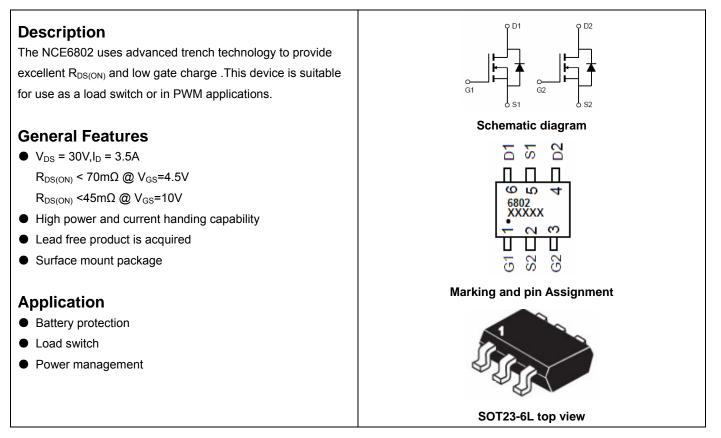


# NCE N-Channel Enhancement Mode Power MOSFET



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6802	NCE6802	SOT-23-6L	Ø180mm	8 mm	3000 units

## Absolute Maximum Ratings (T<sub>A</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	3.5	А
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	20	A
Maximum Power Dissipation	PD	1.2	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	°C

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ extsf{ heta}JA}$	104	°C/W

#### Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30	33	-	V



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Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)			•			J
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.2	1.5	2.2	V
Drain-Source On-State Resistance	5	V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A	-	36	45	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	-	59	70	mΩ
Forward Transconductance	<b>g</b> fs	$V_{DS}$ =5V,I <sub>D</sub> =3.5A	-	12	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,	-	170	-	PF
Output Capacitance	C <sub>oss</sub>	v <sub>DS</sub> =150,v <sub>GS</sub> =00, F=1.0MHz	-	35	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	23	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	4.5	-	nS
Turn-on Rise Time	tr	$V_{DS}$ =15V, R <sub>L</sub> =4.2 $\Omega$	-	1.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =3 $\Omega$	-	18.5	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	15.5	-	nS
Total Gate Charge	Qg		-	4.0	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =15V,I <sub>D</sub> =3.5A,	-	0.75	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	0.65	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3.5A	-	0.8	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	3.5	Α

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**

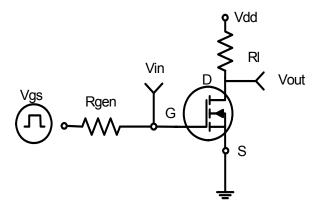


Figure 1:Switching Test Circuit

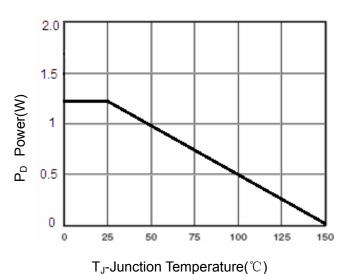
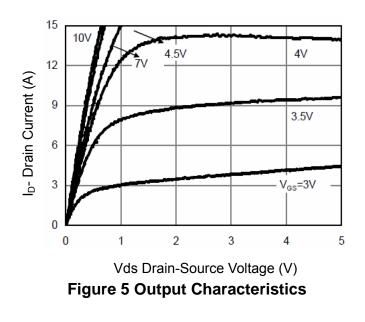
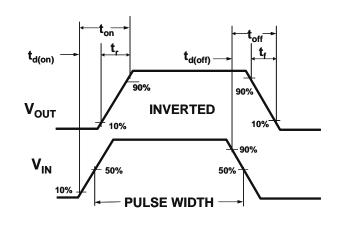


Figure 3 Power Dissipation







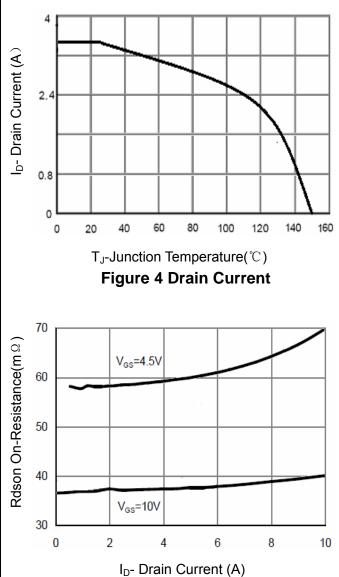
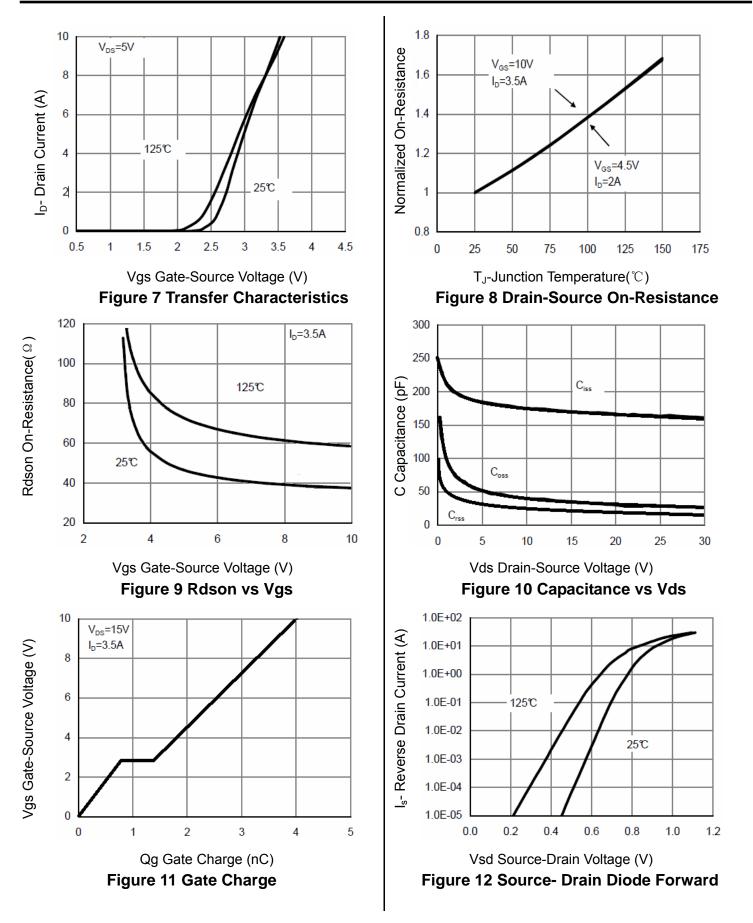


Figure 6 Drain-Source On-Resistance



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# NCE6802





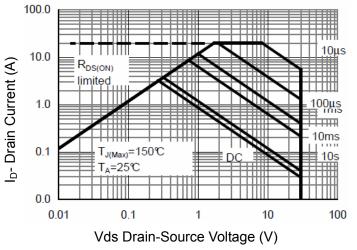


Figure 13 Safe Operation Area

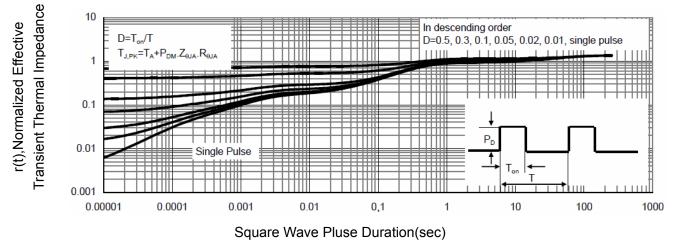
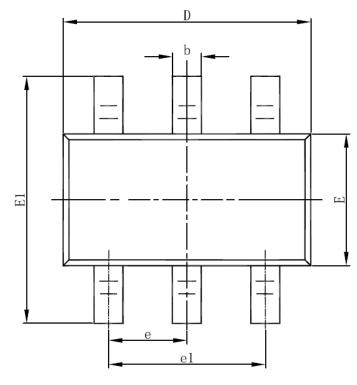
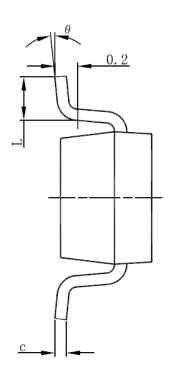


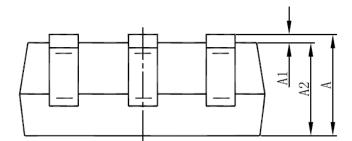
Figure 14 Normalized Maximum Transient Thermal Impedance



# SOT23-6L Package Information







Symbol	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



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